

IN THE CLAIMS:

Please replace claims 9-15, 17, and 18 with the following:

9. (Amended) The method of claim 6, wherein the PVD seed thin film is formed of Al or Cu with a thickness of 2000Å or less at a temperature of 300°C or less and power of 5kW or greater.

10. (Amended) The method of claim 6, wherein the CVD thin film is formed at a thickness of 1000Å or less, and in case where the CVD thin film is of Al, an organic compound, that includes one of dimethyl aluminum hydride (DMAH), $(\text{CH}_3)_2\text{AlH}$, dimethyl ethyl amine alane (DMEAA) and $\text{AlH}_3\text{N}(\text{CH}_3)_2(\text{C}_2\text{H}_5)$, and a first mixture material containing the organic metal compound is used as a precursor.

11. (Amended) The method of claim 10, wherein the CVD thin film is formed at a deposition temperature of 150~300°C and a deposition pressure of 1~100Torr using a second mixture material in which adduct of a small amount is added to DMAH.

12. (Amended) The method of claim 6, wherein the CVD thin film is formed at a thickness of 1000Å or less, and in case where the CVD thin film is of Cu, one of a Lewis-base stabilizing Cu(I)beta-diketonate and a second mixture material containing the Lewis-base stabilizing Cu(I)beta-diketonate is used a precursor.

13. (Amended) The method of claim 12, wherein the CVD thin film is formed at a deposition temperature of 100~300°C and a deposition pressure of 1~100Torr using a third mixture material in which tmvs and Hhfac Dihydrate (HDH) are added to Cu(hfac)(tmvs) as a compound precursor.

14. (Amended) The method of claim 6, wherein, in case where the CVD thin film is formed of Al, the barrier metal layer is formed of Ti, TiN, or a combination of Ti and TiN, where Ti is deposited by ionized PVD process and TiN is deposited by ionized PVD or CVD process.

15. (Amended) The method of claim 6, wherein, in case where the CVD thin film is formed of Cu, the barrier metal layer is formed of either any of Ta, TaN, a combination of Ta and TaN, TiN, and a combination of Ti and TiN, or WNx, where Ta and Ti are deposited by ionized PVD process while TaN, TiN and WNx are deposited by ionized PVD or CVD process.

17. (Amended) The method of claim 6, wherein the PVD reflow thin film is formed by a deposition process performed at a temperature of at least 300°C and one of a power of 5kW so as to perform a subsequent annealing process, and a sequence of a first power of 5kW or greater and a second power of 5kW or less.

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18. (Amended) The method of claim 6, further comprising an ARC layer of a combination of Ti and TiN on the PVD reflow thin film.
